

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-3055.

2. Structure :

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :
 Top side (Anode) : Aluminum alloy .
 Top side (Cathode) : Aluminum alloy .

3. Size :

- 3-1. Chip size : 55 mils × 55 mils (1.4 mm × 1.4 mm).
- 3-2. Chip thickness : 12 ±1.5mils (0.305 ± 0.038 mm).
- 3-3. Active area : 45 mils × 45 mils (1.146 mm × 1.146 mm).
- 3-4. Bonding pad (Anode) : 6 mils × 6 mils (0.153mm× 0.153 mm)
 (Cathode) : 6 mils × 6 mils (0.153mm× 0.153 mm)
- 3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
*Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Open circuit voltage	V_{oc}	$T=2856K$ $E_e=5mW/cm^2$		410		mV
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		15		μA
Reverse light current	I_L	$V_R =5V$ $T=2856K$ $E_e=5mW/cm^2$		15		μA
Total Capacitance	C_t	$V_R =5V$ $E_e=0mW/cm^2$ $f=1MHz$		5		pF

*Based on 100% probing

